

Diagonal 11mm (Type 2/3) CCD Image Sensor for EIA B/W Video Camera

Description

The ICX062AL is an interline CCD solid-state image sensor suitable for EIA black-and-white video cameras with a diagonal 11mm (Type 2/3) system.

High sensitivity is achieved by adopting HAD (Hole-Accumulation Diode) sensors. The chip features a field period readout system and an electronic shutter with variable charge-storage time.

Features

- High resolution
- · Low smear
- · High sensitivity, low dark current
- Excellent antiblooming characteristics
- Continuous variable-speed shutter

Device Structure

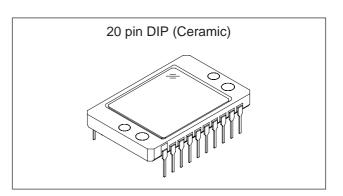
- Image size: Diagonal 11mm (Type 2/3)
- Number of effective pixels: 980 (H) × 494 (V), approx. 480K pixels
- 1038 (H) \times 504 (V), approx. 520K pixels • Total number of pixels:
- Interline CCD image sensor
- Chip size:
- 10.75mm (H) × 8.7mm (V)
- Unit cell size: 9.3µm (H) × 13.6µm (V) Horizontal (H) direction; front 3 pixels, rear 55 pixels
- · Optical black:
- Number of dummy bits:
 - Vertical 1 (even fields only)

Horizontal 25

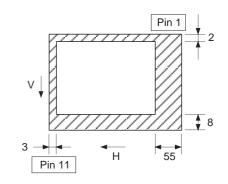
Silicon

Vertical (V) direction;

Substrate material:



ICX062AL

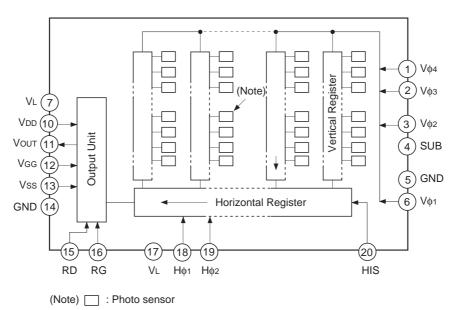


Optical black position (Top View)

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front 8 pixels, rear 2 pixels

Block Diagram and Pin Configuration (Top View)



Pin Description

Pin No.	Symbol	Description	Pin No.	Symbol	Description
1	Vφ4	Vertical register transfer clock	11	Vout	Signal output
2	Vфз	Vertical register transfer clock	12	Vgg	Output amplifier gate bias
3	Vφ2	Vertical register transfer clock	13	Vss	Output amplifier source
4	SUB	Substrate (overflow drain)	14	GND	GND
5	GND	GND	15	RD	Reset drain
6	Vφ1	Vertical register transfer clock	16	RG	Reset gate clock
7	VL	Protective transistor bias	17	VL	Protective transistor bias
8	NC		18	Ηφ1	Horizontal register transfer clock
9	NC		19	Ηφ2	Horizontal register transfer clock
10	Vdd	Output amplifier drain power	20	HIS	Horizontal register input source bias

Absolute Maximum Ratings

	Item	Ratings	Unit	Remarks	
Substrate voltage S	SUB – GND	-0.3 to +55	V		
	HIS, Vdd, RD, Vout, Vss – GND	-0.3 to +20	V		
Supply voltage	HIS, Vdd, RD, Vout, Vss – SUB	-55 to +10	V		
Vertical, horizontal	Vφ1, Vφ2, Vφ3, Vφ4, Hφ1, Hφ2 – GND	-15 to +20	V		
clock input voltage	$V\phi_1, V\phi_2, V\phi_3, V\phi_4, H\phi_1, H\phi_2 - SUB$	-65 to +10	V *1		
Voltage difference	between vertical clock input pins	to +15	V *1		
Voltage difference	between horizontal clock input pins	to +17	V		
Ηφ1, Ηφ2 – Vφ4		-17 to +17	V		
RG, Vgg – GND		-10 to +15	V		
RG, Vgg – SUB		–55 to +10	V		
VL – SUB		-65 to +0.3	V		
Vφ1, Vφ2, Vφ3, Vφ4, Vss, RG, Vgg – Vl	Hφ1, Hφ2, HIS, Vdd, RD, Vout,	-0.3 to +30	V		
Storage temperatur	re	-30 to +80	+80 °C		
Operating temperat	ture	-10 to +60	°C		

 $^{*1}\,$ +27V (max.) when clock width < 10µs and the clock duty factor < 0.1%.

Bias Conditions

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Output amplifier drain voltage	Vdd	14.7	15.0	15.3	V	
Reset drain voltage	Vrd	14.7	15.0	15.3	V	Vrd = Vdd
Output amplifier gate voltage	Vgg	1.6	2.0	2.6	V	
Output amplifier source	Vss		ounded v 0Ω resis			±5%
Substrate voltage adjustment range	Vsuв	9		19	V	*1
Substrate voltage adjustment accuracy	ΔVsub	-3		+3	%	
Reset gate clock voltage adjustment range	Vrgl	0		3.0	V	*1
Reset gate clock voltage adjustment accuracy	ΔV rgl	-3		+3	%	
Protective transistor bias	VL	-13		-10	V	*2
Horizontal register input source bias	VHIS	14.7	15.0	15.3	V	VHIS = VDD

DC Characteristics

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Output amplifier drain current	Idd		5		mA	
Input current	lin1			1	μA	*3
Input current	IIN2			10	μA	*4

^{*1} Indications of substrate voltage (Vsub) and reset gate clock voltage (VRGL) setting value

The setting value of the substrate voltage and reset gate clock voltage are indicated on the back of the image sensor by a special code. Adjust the substrate voltage (Vsub) and reset gate clock voltage (VRGL) to the indicated voltage. The adjustment accuracy is ±3%.

Vsub code – one character indication

VRGL code - one character indication

 $\begin{array}{c} \square \\ \uparrow \end{array} \uparrow$

VRGL code VSUB code

"Code" and optimal setting correspond to each other as follows.

VRGL code	1	2	3	4	5	6	7
Optimal setting	0	0.5	1.0	1.5	2.0	2.5	3.0

Vsub code	D	Е	f	G	h	J	К	L	m	Ν	Ρ	Q	R	S	Т	U	V	W	Х	Y	Ζ
Optimal setting	9.0	9.5	10.0	10.5	11.0	11.5	12.0	12.5	13.0	13.5	14.0	14.5	15.0	15.5	16.0	16.5	17.0	17.5	18.0	18.5	19.0

<Example> "5K" \rightarrow VRGL = 2.0V VSUB = 12.0V

 *2 This must no exceed the VvL voltage of the vertical clock waveform.

- *3 1) Current to each pin when 20V is applied to VDD, RD, VOUT, Vss, HIS, and SUB pins, while pins that are not tested are grounded.
 - 2) Current to each pin when 20V is applied sequentially to V_{\$\phi1\$}, V_{\$\phi2\$}, V_{\$\phi3\$}, V_{\$\phi4\$}, H_{\$\phi1\$}, and H_{\$\phi2\$} pins, while pins that are not tested are grounded. However, 20V is applied to SUB pin.
 - 3) Current to each pin when 15V is applied sequentially to RG and V_{GG} pins, while pins that are not tested are grounded. However, 15V is applied to SUB pin.
 - 4) Current to V_L pin when 30V is applied to all pins except the pin being tested and when V_L pin is grounded. However, GND and SUB pins are left open.

^{*4} Current to SUB pin when 55V is applied to SUB pin, while pins that are not tested are grounded.

Clock Voltage Conditions

Item	Symbol	Min.	Тур.	Max.	Unit	Waveform diagram	Remarks
Readout clock voltage	Vvт	14.5	15.0	15.5	V	1	
	Vvh1, Vvh2, Vvh3, Vvh4	-0.6		0	V	2	Vvh = (Vvh1 + Vvh2)/2
	Vvl1, Vvl2, Vvl3, Vvl4		-9.6		V	2	VvL = (VvL3 + VvL4)/2
	Vφv	8.9			V	2	$V\phi \vee = V \vee Hn - V \vee Ln (n = 1 \text{ to } 4)$
Vertical transfer	I VVH1 – VVH2I			0.2	V	2	
clock voltage	Vvнз — Vvн	-0.5		0	V	2	
	Vvh4 – Vvh	-0.5		0	V	2	
	V∨нн			0.8	V	2	High-level coupling
	Vvhl			1.0	V	2	High-level coupling
	Vvlh			0.8	V	2	Low-level coupling
	Vvll			0.8	V	2	Low-level coupling
Horizontal transfer	Vфн	6.0		8.0	V	3	
clock voltage	Vhl	-4.0		-3.5	V	3	
Reset gate clock	Vørg	6.0		13.0	V	3	*1
voltage	Vrgl	0		3.0	V	3	
Substrate clock voltage	Vфsuв	27.0		32.0	V	4	*2

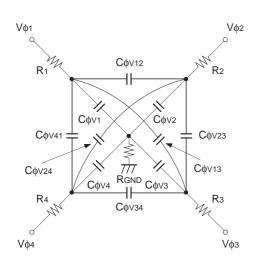
*1 The reset gate clock voltage need not be adjusted when the reset gate clock is driven when the specifications are as given below. In this case, the reset gate clock voltage setting indicated on the back of the image sensor has not significance.

ltem	Symbol	Min.	Тур.	Max.	Unit	Waveform diagram	Remarks
Reset gate clock	Vrgl	-0.2	0	0.2	V	3	
voltage	Vørg	8.5	9.0	9.5	V	3	

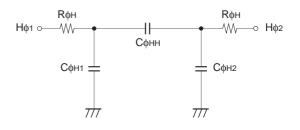
 $^{\ast 2}\,$ The electronic shutter speed must be between 1/60 and 1/2000s.

Clock Equivalent Circuit Constant

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Capacitance between vertical transfer	C φν1, C φν3		2700		pF	
clock and GND	C φν2, C φν4		2700		pF	
	Сфv12, Сфv34		2100		pF	
Capacitance between vertical transfer	Сфv23, Сфv41		900		pF	
clocks	Сфv13		1000		pF	
	Сфv24		500		pF	
Capacitance between horizontal transfer clock and GND	Сфн1, Сфн2		47		pF	
Capacitance between horizontal transfer clocks	Сфнн		58		pF	
Capacitance between reset gate clock and GND	Сфр		7		pF	
Capacitance between substrate clock and GND	Сфѕив		800		pF	
Vertical transfer clock serial resistor	R1, R2, R3, R4		22		Ω	
Vertical transfer clock ground resistor	Rgnd		3		Ω	
Horizontal transfer clock serial resistor	Rфн		10		Ω	



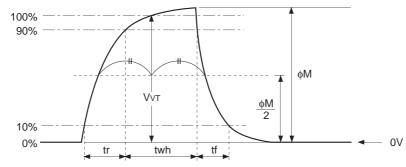
Vertical transfer clock equivalent circuit



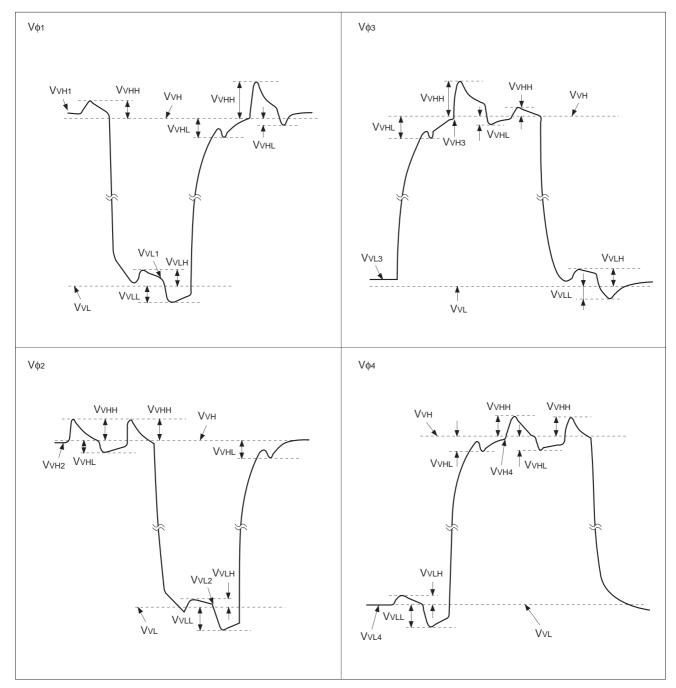
Horizontal transfer clock equivalent circuit

Drive Clock Waveform Conditions

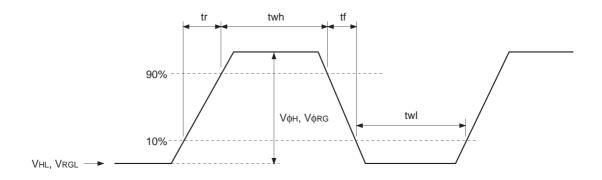
(1) Readout clock waveform



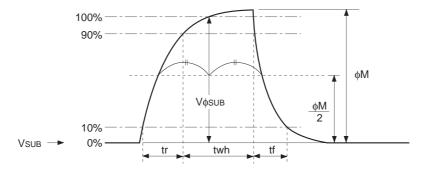




(3) Horizontal transfer clock waveform and reset gate clock waveform



(4) Substrate clock waveform



Clock Switching Characteristics

ltem	Symbol		twh			twl			tr			tf		Unit	Remarks
Item	Symbol	Min.	Тур.	Max.		Remains									
Readout clock	VT		2.4						0.2			0.1		μs	During readout
Vertical transfer clock	Vφ1, Vφ2		62.6			0.74			0.1			0.1		μs	During
	Vø3, Vø4		1.3			62.1			0.1			0.1		μs	imaging
Horizontal	Ηφ		20			20			8			8		ns	During imaging
transfer clock	Ηφı		4.5						0.01			0.01		μs	During
	Ηφ2					4.5			0.01			0.01		μs	parallel-serial conversion
Reset gate clock	φRG		10			41.6			2.0			2.0		ns	
Substrate clock	фЅѠВ		1.9						0.08			0.1		μs	During drain charge

 $(Ta = 25^{\circ}C)$

Image Sensor Characteristics

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Item	Symbol	Min.	Тур.	Max.	Unit	Measurement method	Remarks
Sensitivity	S	350	600		mV	1	
Saturation signal	Vsat	800			mV	2	Ta = 60°C
Smear	Sm		0.0003	0.002	%	3	
Video signal shading	SH			25	%	4	
Dark signal	Vdt			2	mV	5	Ta = 60°C
Dark signal shading	ΔVdt			1	mV	6	Ta = 60°C
Flicker	F			5	%	7	
Lag	Lag			0.5	%	8	

Image Sensor Characteristics Measurement Method

Measurement conditions

- 1) In the following measurements, the substrate voltage and the reset gate clock voltage are set to the values indicated on the device, and the device drive conditions are at the typical values of the bias and clock voltage conditions.
- 2) In the following measurements, spot blemishes are excluded and, unless otherwise specified, the optical black (OB) level is used as the reference for the signal output, and the value measured at point [*A] in the Drive Circuit is used.

O Definition of Standard Imaging Conditions

- Standard imaging condition I: Use a pattern box (luminance 706cd/m², color temperature of 3200K halogen source) as a subject. (Pattern for evaluation is not applicable.) Use a testing standard lens with CM500S (t = 1.0mm) as an IR cut filter and image at F8. The luminous intensity to the sensor receiving surface at this point is defined as the standard sensitivity testing luminous intensity.
- 2) Standard imaging condition II: Image a light source with a uniformity of brightness within 2% at all angles. Use a testing standard lens with CM500S (t = 1.0mm) as an IR cut filter. The luminous intensity is adjusted to the value indicated in each testing item by the lens diaphragm.
- 1. Sensitivity

Set to standard imaging condition I. After selecting the electronic shutter mode with a shutter speed of 1/250s, measure the signal output (Vs) at the center of the screen and substitute the value into the following formula.

$$S = Vs \times \frac{250}{60} [mV]$$

2. Saturation signal

Set to standard imaging condition II. After adjusting the luminous intensity to 10 times the intensity with average value of the signal output is 200mV, measure the minimum value of the signal output.

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3. Smear

Set to standard imaging condition II. With the lens diaphragm at F5.6 to F8, adjust the luminous intensity to 500 times the intensity with average value of the signal output, 200mV. When the readout clock is stopped and the charge drain is executed by the electronic shutter at the respective H blankings, measure the maximum value VSm [mV] of the signal output, and substitute the value into the following formula.

 $Sm = \frac{VSm}{200} \times \frac{1}{500} \times \frac{1}{10} \times 100 \text{ [\%] (1/10V method conversion value)}$

4. Video signal shading

Set to standard imaging condition II. With the lens diaphragm at F5.6 to F8, adjust the luminous intensity so that the average value of the signal output is 200 mV. Then measure the maximum (Vmax [mV]) and minimum (Vmin [mV]) values of the signal output, and substitute the values into the following formula.

 $SH = (Vmax - Vmin)/200 \times 100 [\%]$

5. Dark signal

Measure the average value (Vdt [mV]) of the signal output with the device ambient temperature 60°C and the device in the light-obstructed state, using the horizontal idle transfer level as a reference.

6. Dark signal shading

After measuring 5, measure the maximum (Vdmax [mV]) and minimum (Vdmin [mV]) values of the dark signal output, and substitute the values into the following formula.

 $\Delta Vdt = Vdmax - Vdmin [mV]$

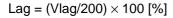
7. Flicker

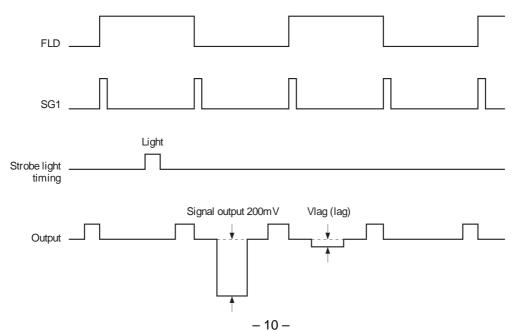
Set to standard imaging condition II. Adjust luminous intensity so that the average value of the signal output is 200mV, and then measure the difference in the signal level between fields (Δ Vf [mV]). Then substitute the value into the following formula.

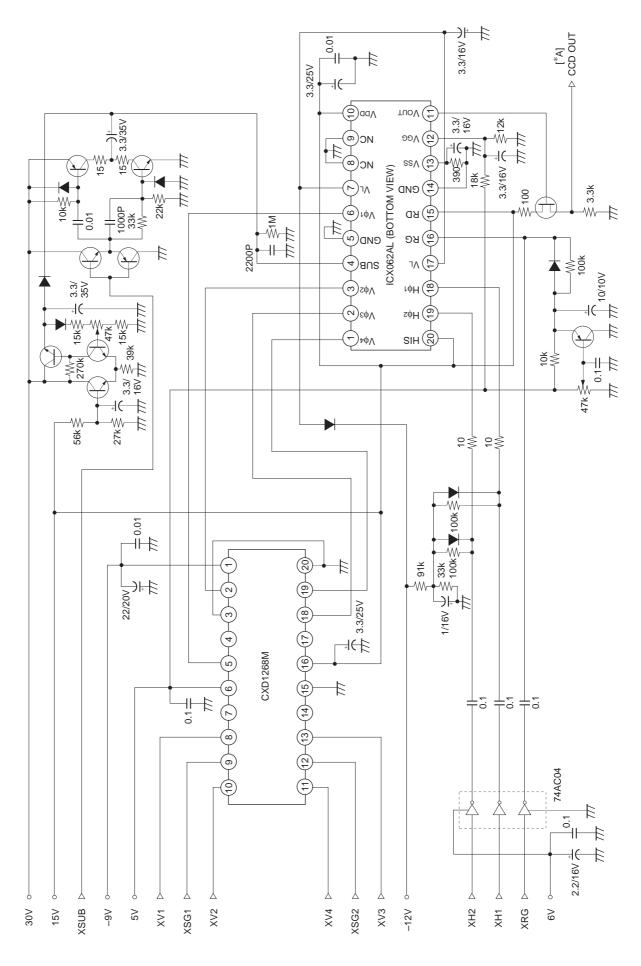
 $F = (\Delta V f/200) \times 100 [\%]$

8. Lag

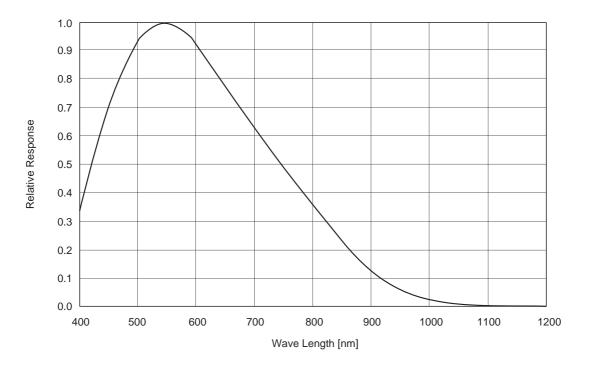
Adjust the signal output value generated by strobe light to 200mV. After setting the strobe light so that it strobes with the following timing, measure the residual signal (Vlag). Substitute the value into the following formula.





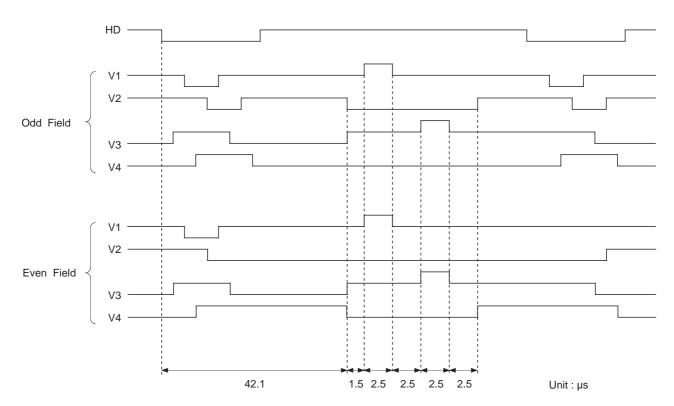


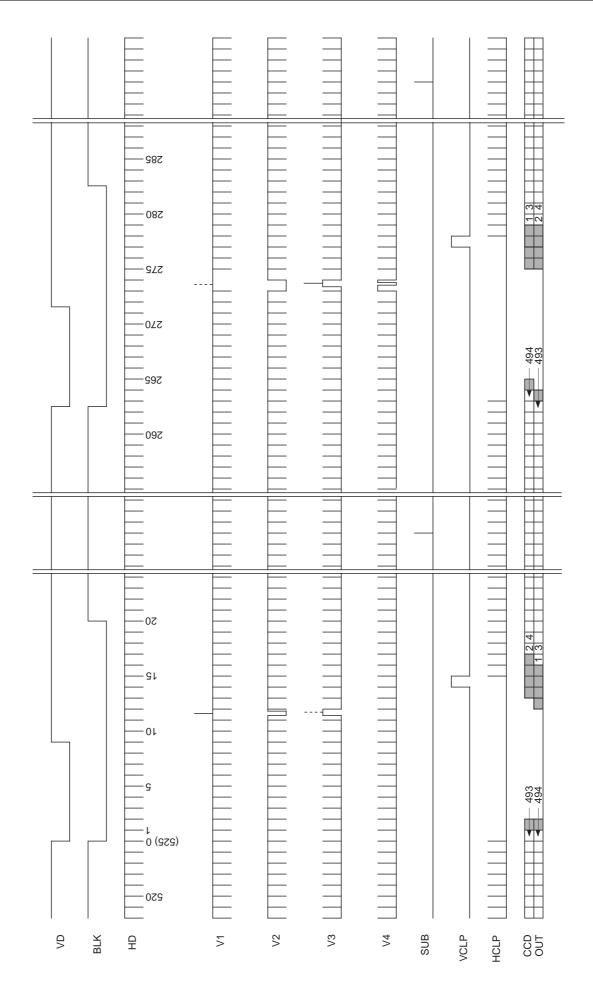




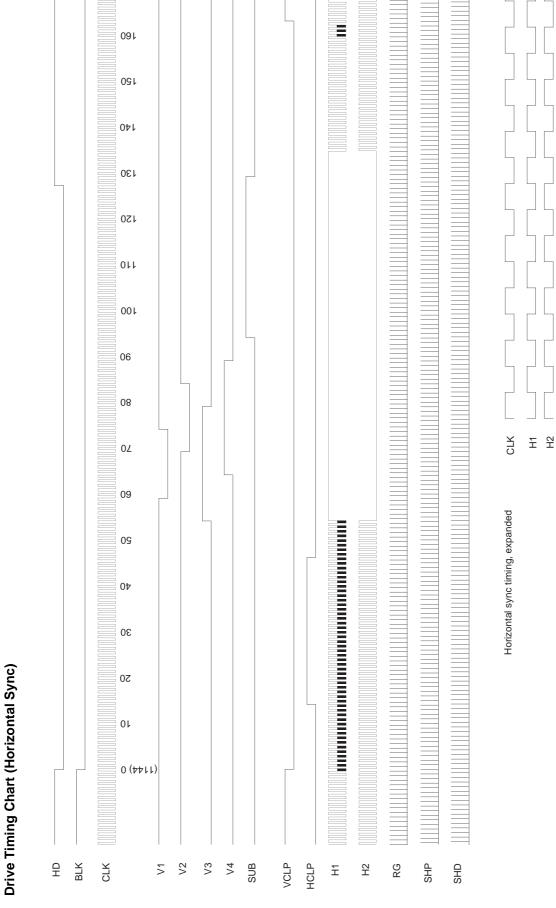
Spectral Sensitivity Characteristics (includes lens characteristics, excludes light source characteristics)

Sensor Readout Clock Timing Chart









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SHD

RG SHP

– 14 –

Notes on Handling

1) Static charge prevention

CCD image sensors are easily damaged by static discharge. Before handling be sure to take the following protective measures.

- a) Either handle bare handed or use non chargeable gloves, clothes or material. Also use conductive shoes.
- b) When handling directly use an earth band.
- c) Install a conductive mat on the floor or working table to prevent the generation of static electricity.
- d) Ionized air is recommended for discharge when handling CCD image sensor.
- e) For the shipment of mounted substrates, use boxes treated for the prevention of static charges.

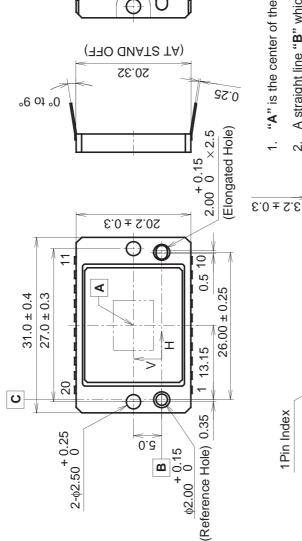
2) Soldering

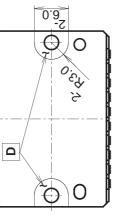
- a) Make sure the package temperature does not exceed 80°C.
- b) Solder dipping in a mounting furnace causes damage to the glass and other defects. Use a grounded 30W soldering iron and solder each pin in less than 2 seconds. For repairs and remount, cool sufficiently.
- c) To dismount an imaging device, do not use a solder suction equipment. When using an electric desoldering tool, use a thermal controller of the zero cross On/Off type and connect it to ground.

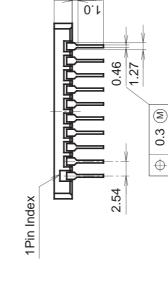
3) Dust and dirt protection

Image sensors are packed and delivered by taking care of protecting its glass plates from harmful dust and dirt. Clean glass plates with the following operation as required, and use them.

- a) Operate in clean environments (around class 1000 is appropriate).
- b) Do not either touch glass plates by hand or have any object come in contact with glass surfaces.
 Should dirt stick to a glass surface, blow it off with an air blower. (For dirt stuck through static electricity ionized air is recommended.)
- c) Clean with a cotton bud and ethyl alcohol if the glass surface is grease stained. Be careful not to scratch the glass.
- d) Keep in a case to protect from dust and dirt. To prevent dew condensation, preheat or precool when moving to a room with great temperature differences.
- e) When a protective tape is applied before shipping, just before use remove the tape applied for electrostatic protection. Do not reuse the tape.
- 4) Do not expose to strong light (sun rays) for long periods. For continuous using under cruel condition exceeding the normal using condition, consult our company.
- 5) Exposure to high temperature or humidity will affect the characteristics. Accordingly avoid storage or usage in such conditions.
- 6) CCD image sensors are precise optical equipment that should not be subjected to too much mechanical shocks.







PACKAGE STRUCTURE

Ceramic	GOLD PLATING	42 ALLOY	5.9g	
PACKAGE MATERIAL	LEAD TREATMENT	LEAD MATERIAL	PACKAGE WEIGHT	

- 1. "A" is the center of the effective image sensor area.
- 2. A straight line "**B**" which passes through the centers of the reference hole and the elongated hole is the reference axis of vertical direction.
- 3. A straight line "**C**" which passes through the center of the reference hole at right angles to vertical reference line "**B**" is the reference axis of horizontal direction.
- 4. The bottom "D" is the height reference. (Two points are specified.)

5.5 ± 0.2

- 5. The center of the effective image area, specified relative to the reference hole is (H, V) = $(13.15, 5.0) \pm 0.15$ mm.
- 6. The angle of rotation relative to the reference line "B" is less than $\pm 1^{\circ}$.
- 7. The height from the bottom "D" to the effective image area is 1.46 ± 0.15 mm.
- 8. Planar orientation of the effective image area relative to the bottom "D" is less than 60µm.
- The thickness of the cover glass is 0.75mm and the refractive index is 1.5.